

CMXT2207

**SURFACE MOUNT  
DUAL COMPLEMENTARY  
SILICON TRANSISTORS**

**SUPERmini™**



**SOT-26 CASE**



[www.centrasemi.com](http://www.centrasemi.com)

**DESCRIPTION:**

The CENTRAL SEMICONDUCTOR CMXT2207 type is a dual complementary silicon transistor manufactured by the epitaxial planar process, epoxy molded in a SUPERmini™ surface mount package, and designed for small signal general purpose and switching applications.

**MARKING CODE: X07**

**MAXIMUM RATINGS: (T<sub>A</sub>=25°C)**

Collector-Base Voltage
Collector-Emitter Voltage
Emitter-Base Voltage
Continuous Collector Current
Power Dissipation
Operating and Storage Junction Temperature
Thermal Resistance

SYMBOL	NPN		PNP		UNITS
V <sub>CBO</sub>	75		60		V
V <sub>CEO</sub>	40		60		V
V <sub>EBO</sub>	6.0		5.0		V
I <sub>C</sub>		600			mA
P <sub>D</sub>		350			mW
T <sub>J</sub> , T <sub>stg</sub>		-65 to +150			°C
θ <sub>JA</sub>		357			°C/W

**ELECTRICAL CHARACTERISTICS PER TRANSISTOR: (T<sub>A</sub>=25°C unless otherwise noted)**

SYMBOL	TEST CONDITIONS	NPN		PNP		UNITS
		MIN	MAX	MIN	MAX	
I <sub>CBO</sub>	V <sub>CB</sub> =60V	-	10	-	-	nA
I <sub>CBO</sub>	V <sub>CB</sub> =50V	-	-	-	10	nA
I <sub>CBO</sub>	V <sub>CB</sub> =60V, T <sub>A</sub> =125°C	-	10	-	-	µA
I <sub>CBO</sub>	V <sub>CB</sub> =50V, T <sub>A</sub> =125°C	-	-	-	10	µA
I <sub>EBO</sub>	V <sub>EB</sub> =3.0V	-	10	-	-	nA
I <sub>CEV</sub>	V <sub>CE</sub> =60V, V <sub>EB</sub> =3.0V	-	10	-	-	nA
I <sub>CEV</sub>	V <sub>CE</sub> =30V, V <sub>BE</sub> =0.5V	-	-	-	50	nA
BV <sub>CBO</sub>	I <sub>C</sub> =10µA	75	-	60	-	V
BV <sub>CEO</sub>	I <sub>C</sub> =10mA	40	-	60	-	V
BV <sub>EBO</sub>	I <sub>E</sub> =10µA	6.0	-	5.0	-	V
V <sub>CE(SAT)</sub>	I <sub>C</sub> =150mA, I <sub>B</sub> =15mA	-	0.3	-	0.4	V
V <sub>CE(SAT)</sub>	I <sub>C</sub> =500mA, I <sub>B</sub> =50mA	-	1.0	-	1.6	V
V <sub>BE(SAT)</sub>	I <sub>C</sub> =150mA, I <sub>B</sub> =15mA	0.6	1.2	-	1.3	V
V <sub>BE(SAT)</sub>	I <sub>C</sub> =500mA, I <sub>B</sub> =50mA	-	2.0	-	2.6	V
h <sub>FE</sub>	V <sub>CE</sub> =10V, I <sub>C</sub> =0.1mA	35	-	75	-	
h <sub>FE</sub>	V <sub>CE</sub> =10V, I <sub>C</sub> =1.0mA	50	-	100	-	
h <sub>FE</sub>	V <sub>CE</sub> =10V, I <sub>C</sub> =10mA	75	-	100	-	
h <sub>FE</sub>	V <sub>CE</sub> =10V, I <sub>C</sub> =150mA	100	300	100	300	
h <sub>FE</sub>	V <sub>CE</sub> =1.0V, I <sub>C</sub> =150mA	50	-	-	-	
h <sub>FE</sub>	V <sub>CE</sub> =10V, I <sub>C</sub> =500mA	40	-	50	-	
f <sub>T</sub>	V <sub>CE</sub> =20V, I <sub>C</sub> =20mA, f=100MHz	300	-	-	-	MHz
f <sub>T</sub>	V <sub>CE</sub> =20V, I <sub>C</sub> =50mA, f=100MHz	-	-	200	-	MHz

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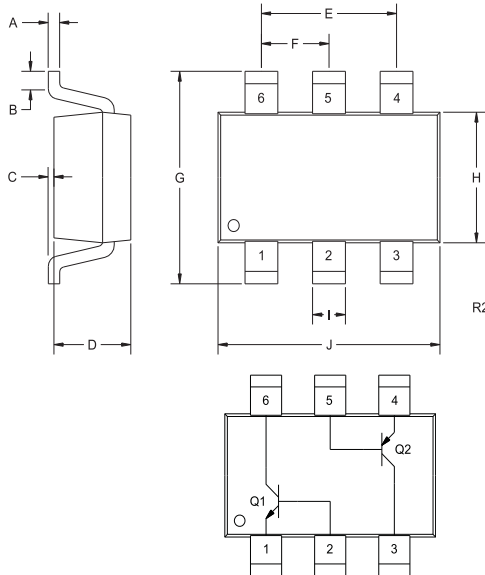
**SURFACE MOUNT  
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**ELECTRICAL CHARACTERISTICS PER TRANSISTOR - Continued:** ( $T_A=25^\circ\text{C}$  unless otherwise noted)

SYMBOL	TEST CONDITIONS	NPN		PNP		UNITS
		MIN	MAX	MIN	MAX	
$C_{ob}$	$V_{CB}=10\text{V}, I_E=0, f=1.0\text{MHz}$	-	8.0	-	8.0	pF
$C_{ib}$	$V_{EB}=0.5\text{V}, I_C=0, f=1.0\text{MHz}$	-	25	-	-	pF
$C_{ib}$	$V_{EB}=2.0\text{V}, I_C=0, f=1.0\text{MHz}$	-	-	-	30	pF
$h_{ie}$	$V_{CE}=10\text{V}, I_C=1.0\text{mA}, f=1.0\text{kHz}$	2.0	8.0	-	-	k $\Omega$
$h_{ie}$	$V_{CE}=10\text{V}, I_C=10\text{mA}, f=1.0\text{kHz}$	0.25	1.25	-	-	k $\Omega$
$h_{re}$	$V_{CE}=10\text{V}, I_C=1.0\text{mA}, f=1.0\text{kHz}$	-	8.0	-	-	$\times 10^{-4}$
$h_{re}$	$V_{CE}=10\text{V}, I_C=10\text{mA}, f=1.0\text{kHz}$	-	4.0	-	-	$\times 10^{-4}$
$h_{fe}$	$V_{CE}=10\text{V}, I_C=1.0\text{mA}, f=1.0\text{kHz}$	50	300	-	-	
$h_{fe}$	$V_{CE}=10\text{V}, I_C=10\text{mA}, f=1.0\text{kHz}$	75	375	-	-	
$h_{oe}$	$V_{CE}=10\text{V}, I_C=1.0\text{mA}, f=1.0\text{kHz}$	5.0	35	-	-	$\mu\text{S}$
$h_{oe}$	$V_{CE}=10\text{V}, I_C=10\text{mA}, f=1.0\text{kHz}$	25	200	-	-	$\mu\text{S}$
$rb'C_c$	$V_{CB}=10\text{V}, I_E=20\text{mA}, f=31.8\text{MHz}$	-	150	-	-	ps
NF	$V_{CE}=10\text{V}, I_C=100\text{mA}, R_S=1.0\text{k}\Omega, f=1.0\text{kHz}$	-	4.0	-	-	dB
$t_{on}$	$V_{CC}=30\text{V}, V_{BE}=0.5\text{V}, I_C=150\text{mA}, I_{B1}=15\text{mA}$	-	-	-	45	ns
$t_d$	$V_{CC}=30\text{V}, V_{BE}=0.5\text{V}, I_C=150\text{mA}, I_{B1}=15\text{mA}$	-	10	-	10	ns
$t_r$	$V_{CC}=30\text{V}, V_{BE}=0.5\text{V}, I_C=150\text{mA}, I_{B1}=15\text{mA}$	-	25	-	40	ns
$t_{off}$	$V_{CC}=6.0\text{V}, I_C=150\text{mA}, I_{B1}=I_{B2}=15\text{mA}$	-	-	-	100	ns
$t_s$	$V_{CC}=30\text{V}, I_C=150\text{mA}, I_{B1}=I_{B2}=15\text{mA}$	-	225	-	-	ns
$t_s$	$V_{CC}=6.0\text{V}, I_C=150\text{mA}, I_{B1}=I_{B2}=15\text{mA}$	-	-	-	80	ns
$t_f$	$V_{CC}=30\text{V}, I_C=150\text{mA}, I_{B1}=I_{B2}=15\text{mA}$	-	60	-	-	ns
$t_f$	$V_{CC}=6.0\text{V}, I_C=150\text{mA}, I_{B1}=I_{B2}=15\text{mA}$	-	-	-	30	ns

**SOT-26 CASE - MECHANICAL OUTLINE**



SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.004	0.007	0.11	0.19
B	0.016	-	0.40	-
C	-	0.004	-	0.10
D	0.039	0.047	1.00	1.20
E	0.074	0.075	1.88	1.92
F	0.037	0.038	0.93	0.97
G	0.102	0.118	2.60	3.00
H	0.059	0.067	1.50	1.70
I	0.016	-	0.41	-
J	0.110	0.118	2.80	3.00

SOT-26 (REV: R2)

**LEAD CODE:**

- 1) Emitter Q1
- 2) Base Q1
- 3) Collector Q2
- 4) Emitter Q2
- 5) Base Q2
- 6) Collector Q1

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